

PATENT / DOCKET NO.: 24061.142

CUSTOMER NO.: 27683

INVENTOR'S DECLARATION FOR PATENT APPLICATION

As below named inventors, we hereby declare that:

Our residence, post office address and citizenship are as stated below next to our names;

We believe we are the original, first and sole joint inventors of the subject matter which is claimed and for which a patent is sought on the invention entitled

METHOD FOR FORMING DIELECTRIC BARRIER LAYER IN DAMASCENE STRUCTURE

the specific	cation of which: (check one)	
	is attached hereto.	
_X	was filed on September 9, 200 under Attorney's Docket Num as Application Serial No. 10/6 and was amended on	ber 24061.142
	state that we have reviewed and unthe claims, as amended by any amen	derstand the contents of the above identified specification, dment referred to above.
in accordar which beca	nce with 37 CFR 1.56, including for	ion which is material to the patentability of this application continuation-in-part applications, material information e of the prior application and the national or PCT part application.
made on ir the knowled both, unde	nformation and belief are believed to edge that willful false statements and	rein of our own knowledge are true and that all statements be true; and further that these statements were made with I the like so made are punishable by fine or imprisonment, oul false statements may jeopardize the validity of the
-	v claim the benefit under Title 35, Unn(s) listed below.	nited States Code, § 119(e) of any United States provisional
(Application	on Number)	(Filing Date)
We hereby	, alaim faraian nriarity hanafita unda	or 25 U.S.C. 110(a) (d) or (f) or 265(h) of any foreign

We hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or (f), or 365(b) of any foreign applications for patent, inventor's or plant breeder's rights certificate(s), or 365(a) of any PCT international application which designated at least one country other than the United States of America, listed below,

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any foreign application for patent, inventor's or plant breeder's rights certificate(s), or any PCT international application having a filing date before that of the application on which priority is claimed.

Prior Foreign Application Number(s)	Country	Foreign Filing Date (MM/DD/YYYY)	Priority Claimed
FULL NAME OF INVE	NTOR: Ai-Sen Liu		
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RESIDENCE: 5F-1,	N. 286, Gong-Yua	n Rd., Hsinohu, Taiwo	u.n.
CITIZENSHIP: Repub	lic of China	,	
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